LGE3D06065A

Silicon Carbide Schottky Diode

V_R = 650 V
I_F = 6A (T_C=150ºC)
Qc = 15nC (V_R=400V)

Features

- Zero Forward/Reverse Recovery
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on V_F
- Temperature Independent Switching Behavior
- 100% avalanche tested

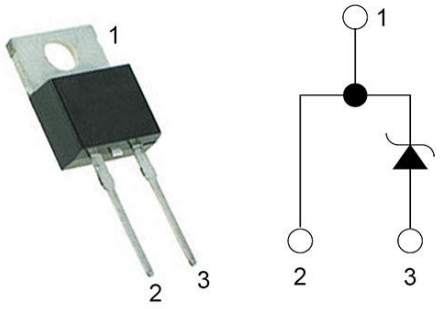
Benefits

- High System Efficiency
- Parallel Device Convenience
- High Temperature Application
- High Frequency Operation
- Hard Switching & High Reliability
- Environmental Protection

Applications

- Switch Mode Power Supplies
- Solar Inverters
- DC/DC converters
- Uninterruptable power supplies

TO-220AC



Part Number	Package	Marking
LGE3D06065A	TO-220AC	LGE3D06065A

Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		650	V
Peak Reverse Surge Voltage	V_{RSM}		650	V
DC Blocking Voltage	V_R		650	V
Continuous Forward Current	I_F	Tc=25˚C Tc=135˚C Tc=150˚C	19 8 6	A
Non repetitive Forward Surge Current	I_{FSM}	T_C = 25°C, t_p=10 ms, Half Sine Pulse T_C = 110°C, t_p=10 ms, Half Sine Pulse T_C = 25°C, t_p=10 µs, Square	40 35 300	A
Repetitive peak Forward Surge Current	I_{FRM}	T_C = 25°C, t_p=10 ms, Freq = 0.1Hz, 100 cycles, Half Sine Pulse T_C = 110°C, t_p=10 ms, Freq = 0.1Hz, 100 cycles, Half Sine Pulse	35 30	A
Total power dissipation	P_D	T_C=25°C	68	W
Operating Junction Temperature	T_J		-55 to 175	°C
Storage Temperature	T_{STG}		-55 to 175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
DC Blocking Voltage	V_{DC}	I_R = 250μA,T_J = 25°C	650			V
Forward Voltage	V_F	I_F = 6A, T_J = 25°C		1.45	1.8	V
		I_F = 6A, T_J = 125°C		1.6		
		I_F = 6A, T_J = 175°C		1.75		
Reverse Current	I_R	V_R = 650V, T_J = 25°C		7	80	μA
		V_R = 650V, T_J = 125°C		38		
		V_R = 650V, T_J = 175°C		108		
Total Capacitive Charge	Q_C	V_R = 400V		15		nC
Total Capacitance	C	V_R = 1V, T_J = 25°C, Freq = 1MHz		230		pF
		V_R = 200V, T_J = 25°C, Freq = 1MHz		33		
		V_R = 400V, T_J = 25°C, Freq = 1MHz		24		

Thermal Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal Resistance	$R_{th(j-c)}$	junction-case		1.8		^{0}C/W

Typical Electrical Curves

Figure 1. Forward Characteristics

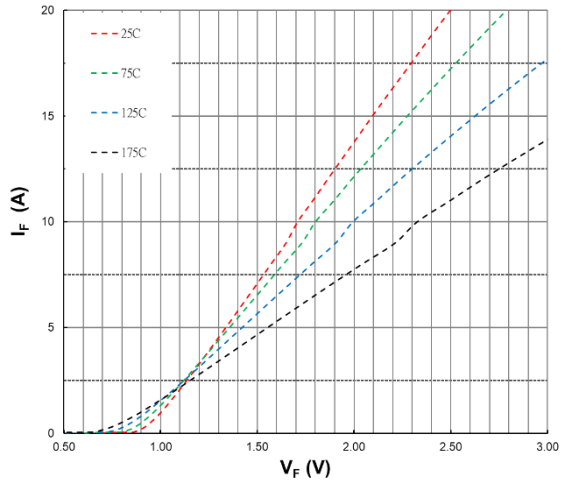


Figure 2. Forward Characteristics

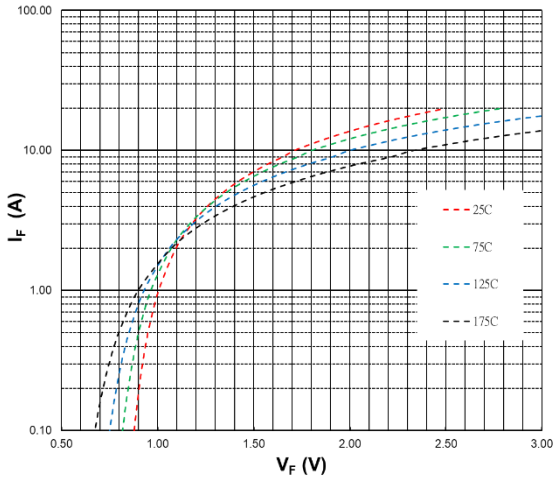


Figure 3. Reverse Characteristics

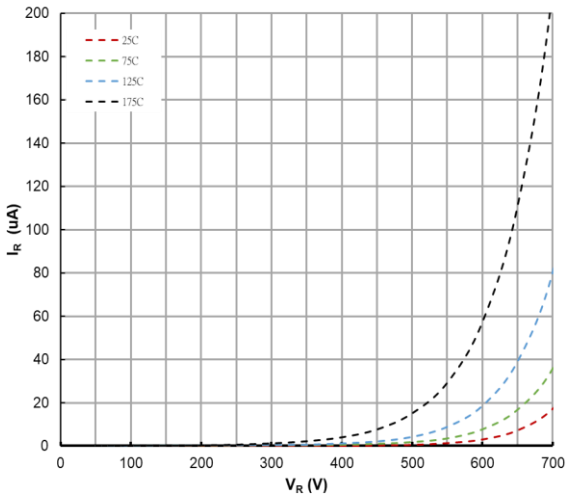


Figure 4. Power Derating

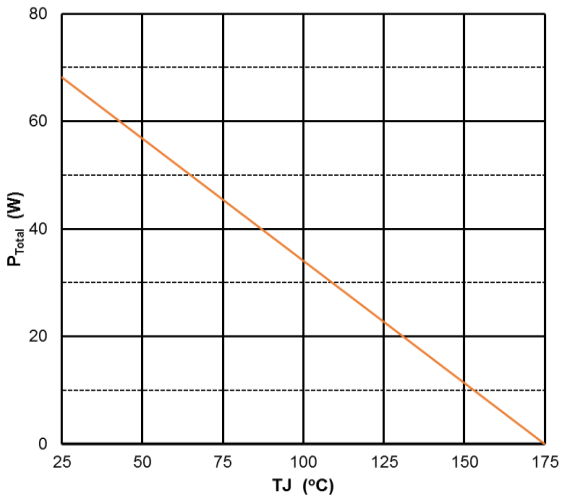


Figure 5. Capacitance vs Reverse Voltage

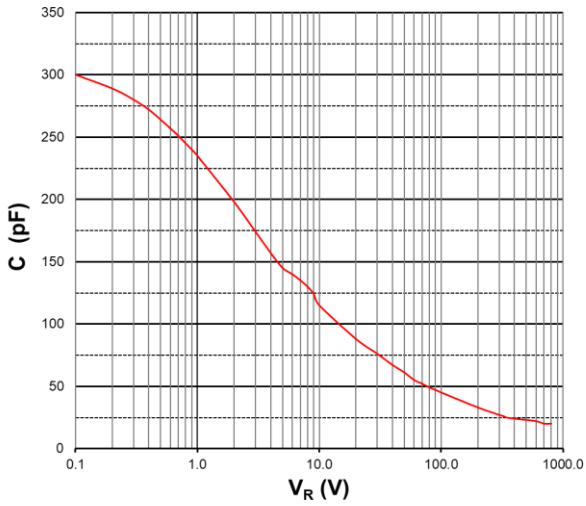
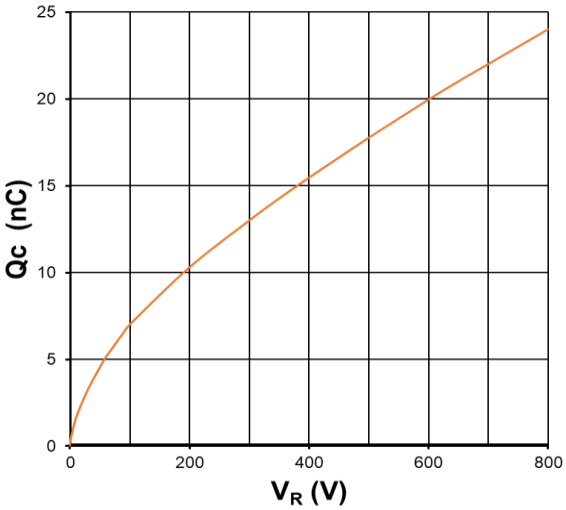


Figure 6. Recovery Charge vs Reverse Voltage



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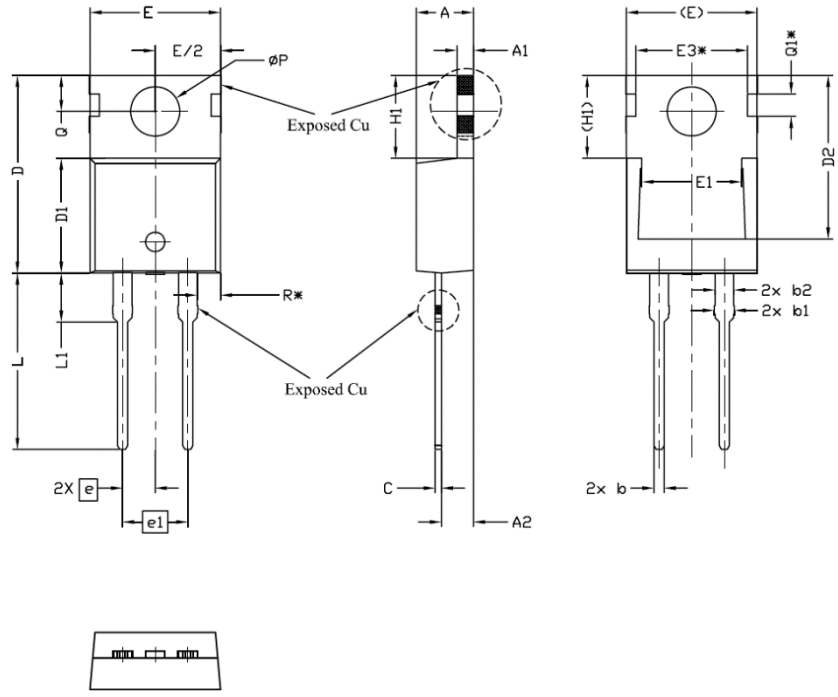
Package Dimensions

(TO-220AC Package)



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
c	0.40	0.50	0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.43	12.73	12.83	5
E	9.96	10.16	10.36	4,5
E1	6.86	7.77	8.89	5
E3*	8.70REF.			
e	2.54BSC			
e1	5.08BSC			
H1	6.30	6.45	6.60	5,6
L	13.47	13.72	13.97	
L1	3.60	3.80	4.00	
ØP	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*	1.73REF.			
R*	1.82REF.			

Note:
1. Package Reference: JEDEC TO220, Variation AB.
2. All Dimensions Are In mm.
3. Slot Required, Notch May Be Rounded
4. Dimension D & E Do Not Include Mold Flash. Mold Flash Shall Not Exceed 0.127mm Pre Side. These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
5. Thermal Pad Contour Optional Within Dimensions E, H1, D2 & E1.
6. Dimension E2 & H1 Define A Zone Where Stamping And Singulation Irregularities Are Allowed.
7. "*" is reference .

Packge	Packing	Box Size L×W×H(mm)	Quatity(pcs/box)	Carton Size L×W×H(mm)	Quatity(pcs/carton)
TO-220AC	50pcs/Tube	558×148×38	1000	565×225×175	5000